

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
07 September 2023 (07.09.2023)



(10) International Publication Number
WO 2023/165914 A1

- (51) **International Patent Classification:**
G03F 7/004 (2006.01) *G03F 7/039* (2006.01)
- (21) **International Application Number:**
PCT/EP2023/054781
- (22) **International Filing Date:**
27 February 2023 (27.02.2023)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
2022-031158 01 March 2022 (01.03.2022) JP
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- (81) **Designated States** (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

- (84) **Designated States** (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:
— with international search report (Art. 21(3))

- (54) **Title:** ION IMPLANTATION THICK FILM RESIST COMPOSITION, METHOD FOR MANUFACTURING PROCESSED SUBSTRATE USING THE SAME AND METHOD FOR MANUFACTURING DEVICE USING THE SAME

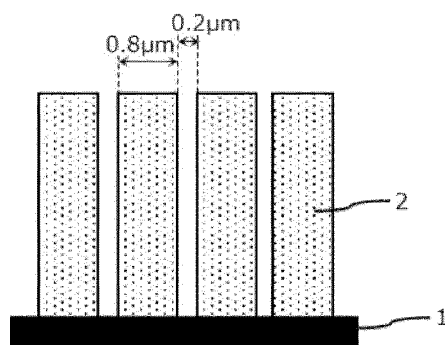


Figure 1

- (57) **Abstract:** [Problem] An ion implantation thick film resist composition is provided. [Means for Solution] An ion implantation thick film resist composition comprising a polymer (A) having a certain structure, a photoacid generator (B) and a solvent (C), wherein the film thickness of the resist film formed from the composition is 1.0 to 50 μm; and the mass average molecular weight of the polymer (A) is 5,000 to 19,000.

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